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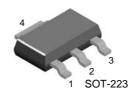
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January 2007

NZT605 NPN Darlington Transistor

- · This device designed for applications requiring extremely high gain at collector currents to 1.0A and high breakdown voltage.
- · Sourced from process 06.



1. Base 2.4. Collector 3. Emitter

Absolute Maximum Ratings * T_C = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	110	V
V _{CBO}	Collector-Base Voltage	140	V
V _{EBO}	Emitter-Base Voltage	10	V
I _C	Collector Current - Continuous	1.5	A
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*} These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Electrical Characteristics * $T_C = 25$ °C unless otherwise noted

Parameter	Conditions	Min.	Max	Units			
Off Characteristics							
Collector-Emitter Breakdown Voltage *	I _C = 10mA, I _B = 0	110		V			
Collector-Base Breakdown Voltage	$I_C = 100 \mu A, I_E = 0$	140		V			
Emitter-Base Breakdown Voltage	$I_E = 100 \mu A, I_C = 0$	10		V			
Collector Cutoff Current	V _{CB} = 120V, I _E = 0		10	nA			
Collector Cutoff Current	V _{CE} = 120V, I _E = 0		10	nA			
Emitter Cut-off Current	$V_{EB} = 8.0V, I_{C} = 0$		100	nA			
ristics *							
DC Current Gain	$V_{CE} = 5.0V$, $I_{C} = 50mA$ $V_{CE} = 5.0V$, $I_{C} = 500mA$ $V_{CE} = 5.0V$, $I_{C} = 1.0A$ $V_{CE} = 5.0V$, $I_{C} = 1.5A$ $V_{CE} = 5.0V$, $I_{C} = 2.0A$	2000 5000 2000 300 200	100K				
Collector-Emitter Saturation Voltage	I _C = 250mA, I _B = 0.25mA I _C = 1.0A, I _B = 1.0mA		1 1.5	V			
Base-Emitter Saturation Voltage	I _C = 1.0A, I _B = 1.0mA		1.8	V			
Base-Emitter On Voltage	I _C = 1.0A, V _{CE} = 5.0V		1.7	V			
characteristics				•			
Transition Frequency	I _C = 100mA, V _{CE} = 10V, f = 20MHz	150		MHz			
	Collector-Emitter Breakdown Voltage * Collector-Base Breakdown Voltage Emitter-Base Breakdown Voltage Collector Cutoff Current Collector Cutoff Current Emitter Cut-off Current Cistics * DC Current Gain Collector-Emitter Saturation Voltage Base-Emitter On Voltage Characteristics	Collector-Emitter Breakdown Voltage * $I_C = 10$ mA, $I_B = 0$ Collector-Base Breakdown Voltage $I_C = 100$ µA, $I_C = 0$ Emitter-Base Breakdown Voltage $I_C = 100$ µA, $I_C = 0$ Collector Cutoff Current $I_C = 100$ µA, $I_C = 0$ Collector Cutoff Current $I_C = 100$ µA, $I_C = 0$ Emitter Cut-off Current $I_C = 100$ µA, $I_C = 0$ Emitter Cut-off Current $I_C = 100$ µA, $I_C = 0$ Emitter Cut-off Current $I_C = 100$ µA, $I_C = 0$ Emitter Cut-off Current $I_C = 100$ µC	Collector-Emitter Breakdown Voltage * $I_C = 10$ mA, $I_B = 0$ 110 Collector-Base Breakdown Voltage $I_C = 100$	Collector-Emitter Breakdown Voltage * $I_C = 10 \text{mA}, I_B = 0$ 110 Collector-Base Breakdown Voltage $I_C = 100 \mu A, I_C = 0$ 140 Emitter-Base Breakdown Voltage $I_C = 100 \mu A, I_C = 0$ 10 Collector Cutoff Current $V_{CB} = 120 V, I_C = 0$ 10 Collector Cutoff Current $V_{CB} = 120 V, I_C = 0$ 10 Emitter Cut-off Current $V_{CB} = 8.0 V, I_C = 0$ 100 Fistics * DC Current Gain $V_{CC} = 5.0 V, I_C = 500 \text{mA}, I_C = 1.00 \text{m}}{V_{CC} = 5.0 V, I_C = 1.00 \text{m}}{V_{CC} = 5.0 V, I_C = 1.00 \text{m}}{V_{CC} = 5.0 V, I_C = 2.00 \text{m}}{V_{CC} = 5.0 V, I_C = 2.00 \text{m}}{V_{CC} = 5.0 V, I_C = 1.00 \text{m}}{V_{CC} = 5.0 V, I_C = 2.00 \text{m}}{V_{CC} = 5.0 V, I_C = 5.0 V}{V_{CC} = 5.0 $			

^{*} Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2.0%

^{1.} These ratings are based on a maximum junction temperature of 150 degrees C.

2. These are steady limits. The factory should be consulted on application involving pulsed or low duty cycle operations

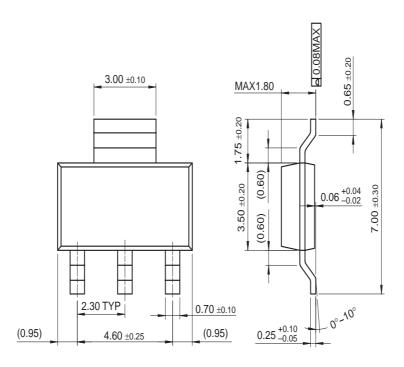
Thermal Characteristics $T_a = 25$ °C unless otherwise noted

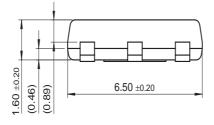
Symbol	Parameter	Max.	Units
P _D	Total Device Dissipation Derate above 25°C	1,000 8.0	mW mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	125	°C/W

^{*} Device mounted on FR-4PCB 36mm \times 18mm \times 1.5mm; mounting pad for the collector lead min. 6cm²

Mechanical Dimensions

SOT-223





Dimensions in Millimeters

UniFET™

 VCX^{TM}

Wire™



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Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.

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Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)

Факс: 8 (812) 320-02-42

Электронная почта: org@eplast1.ru

Адрес: 198099, г. Санкт-Петербург, ул. Калинина,

дом 2, корпус 4, литера А.